

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **MRF314** is Designed for Class C Power Amplifier Applications up to 200 MHz.

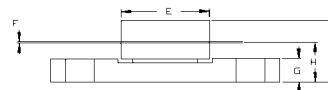
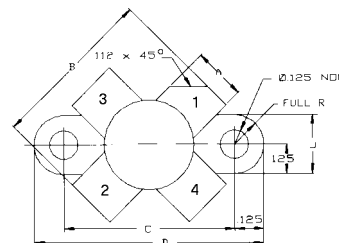
FEATURES:

- $P_G = 10$ dB min. at 30 W/ 150 MHz
- Withstands **30:1** Load VSWR
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	3.4 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	82 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.13 °C/W

PACKAGE STYLE .380 4L FLG



	1970-1980 (1970-1979)	1980-1984 (1980-1984)
A	208/19,33	230/19,84
B	285/19,94	
C	178/18,78	231/19,54
D	370/24,4	500/24,85
E		380/19,18
F	304/21,2	336/21,38
G	385/23,6	375/23,67
H	161/14,86	206/14,53
I		250/23,3
J	242/16,37	233/16,48

ORDER CODE: ASI10872

CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 30\text{ mA}$	35			V
BV_{CES}	$I_C = 30\text{ mA}$	65			V
BV_{EBO}	$I_E = 3.0\text{ mA}$	4.0			V
I_{CBO}	$V_E = 30\text{ V}$			3.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 1.5\text{ A}$	20		80	---
C_{OB}	$V_{CB} = 30\text{ V}$ $f = 1.0\text{ MHz}$		30	40	pF
P_G	$V_{CC} = 28\text{ V}$ $P_{OUT} = 30\text{ W}$ $f = 150\text{ MHz}$	10	13.5		dB
η_c		50			%
ψ		30:1 all phase angles, no degradation in output.			

ADVANCED SEMICONDUCTOR, INC.

7525 ETHEL AVENUE • NORTH HOLLYWOOD, CA 91605 • (818) 982-1200 • FAX (818) 765-3004

REV. A

1/1

Specifications are subject to change without notice.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[Advanced Semiconductor, Inc.:](#)

[MRF314](#)